To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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BB102C

Build in Biasing Circuit MOS FET IC
UHF RF Amplifier

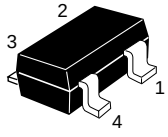
ADE-208-588 (Z)
1st. Edition
November 1997

Features

- Build in Biasing Circuit; To reduce using parts cost & PC board space.
- Low noise characteristics;
  (NF = 2.1 dB typ. at f = 900 MHz)
- Withstanding to ESD;
  Build in ESD absorbing diode. Withstand up to 200V at C=200pF, Rs=0 conditions.
- Provide mini mold packages; CMPAK-4(SOT-343mod)

Outline

CMPAK-4



1. Source
2. Gate1
3. Gate2
4. Drain

- Note 1 Marking is “BW–”.
- Note 2 BB302C is individual type number of HITACHI BBFET.

Absolute Maximum Ratings (Ta = 25°C)

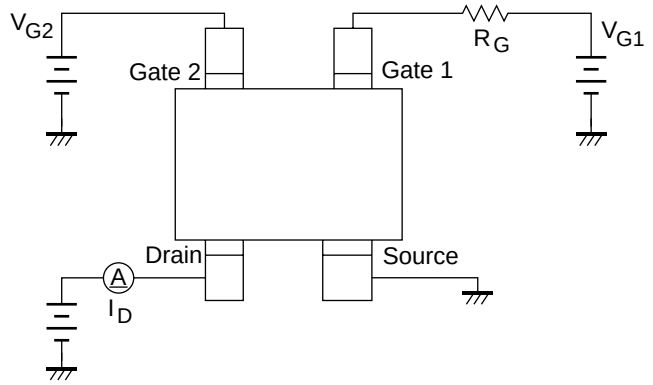
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	12	V
Gate1 to source voltage	V_{G1S}	+10 –0	V
Gate2 to source voltage	V_{G2S}	±10	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

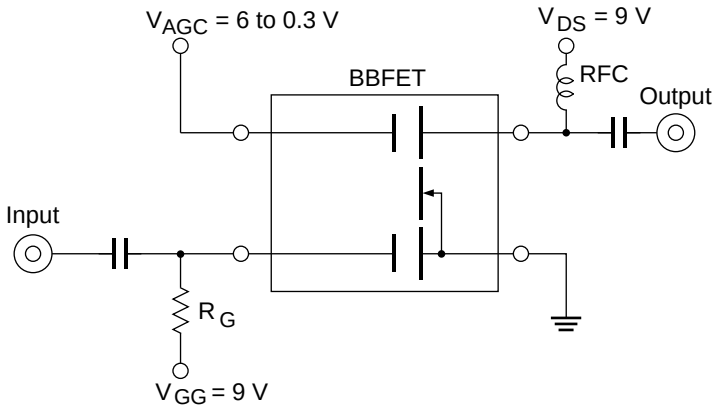
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	12	—	—	V	I_D = 200µA, V_{G1S} = V_{G2S} = 0
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+10	—	—	V	I_{G1} = +10µA, V_{G2S} = V_{DS} = 0
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	±10	—	—	V	I_{G2} = ±10µA, V_{G1S} = V_{DS} = 0
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	V_{G1S} = +9V, V_{G2S} = V_{DS} = 0
Gate2 to source cutoff current	I_{G2SS}	—	—	±100	nA	V_{G2S} = ±9V, V_{G1S} = V_{DS} = 0
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.1	—	0.8	V	V_{DS} = 9V, V_{G2S} = 6V, I_D = 100µA
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.5	—	1.1	V	V_{DS} = 9V, V_{G1S} = 9V, I_D = 100µA
Drain current	$I_{D(op)}$	10	15	20	mA	V_{DS} = 9V, V_{G1} = 9V, V_{G2S} = 6V R_G = 560kΩ
Forward transfer admittance	$\|y_{fs}\|$	16	21	—	mS	V_{DS} = 9V, V_{G1} = 9V, V_{G2S} =6V R_G = 560kΩ, f = 1kHz
Input capacitance	c_{iss}	1.2	1.6	2.2	pF	V_{DS} = 9V, V_{G1} = 9V
Output capacitance	c_{oss}	0.7	1.1	1.5	pF	V_{G2S} =6V, R_G = 560kΩ
Reverse transfer capacitance	c_{rss}	—	0.011	0.03	pF	f = 1MHz
Power gain	PG	16	20	—	dB	V_{DS} = 9V, V_{G1} = 9V, V_{G2S} =6V
Noise figure	NF	—	2.1	3.1	dB	R_G = 120kΩ, f = 900MHz

Main Characteristics

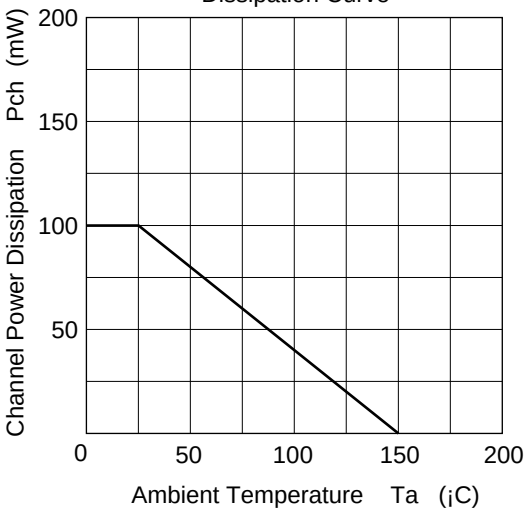
Test Circuit for Operating Items ($I_{D(op)}$, |yfs|, Ciss, Coss, Crss, NF, PG)



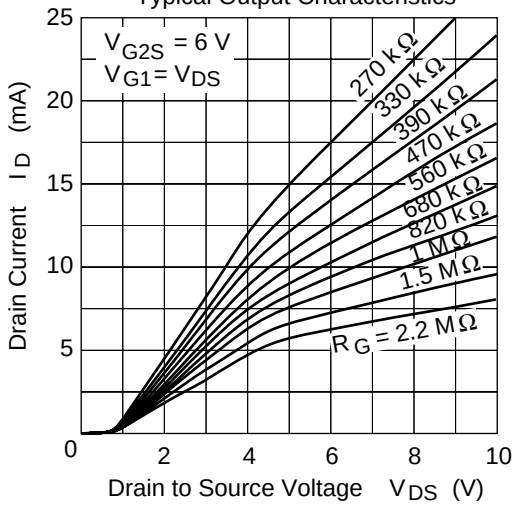
Application Circuit



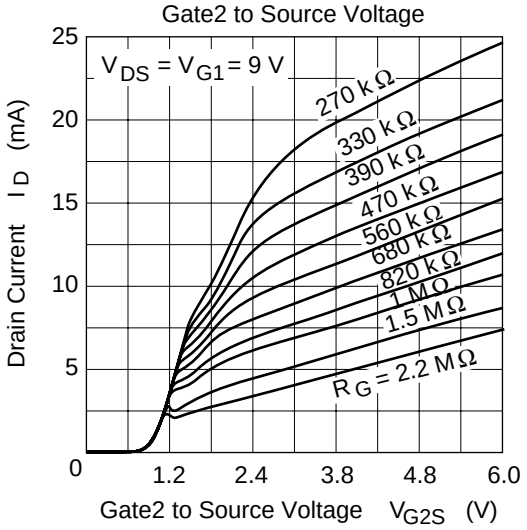
Maximum Channel Power Dissipation Curve



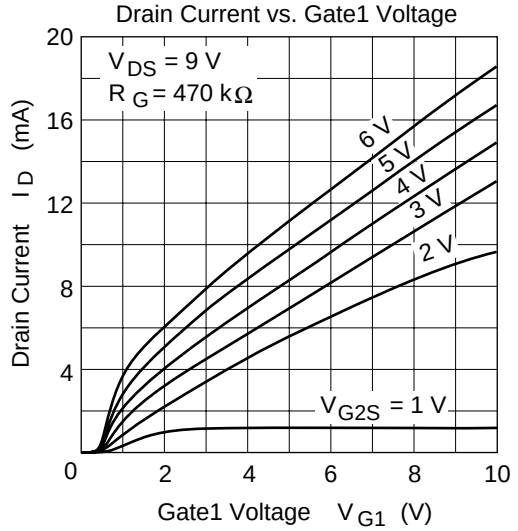
Typical Output Characteristics



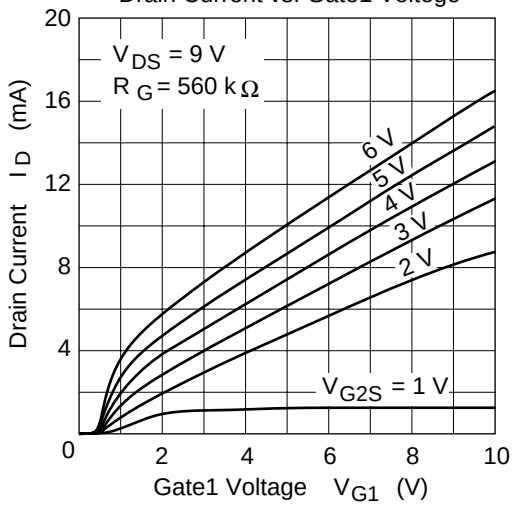
Drain Current vs. Gate2 to Source Voltage



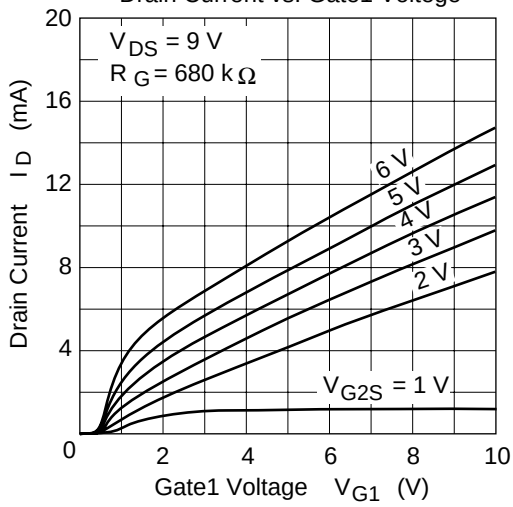
Drain Current vs. Gate1 Voltage



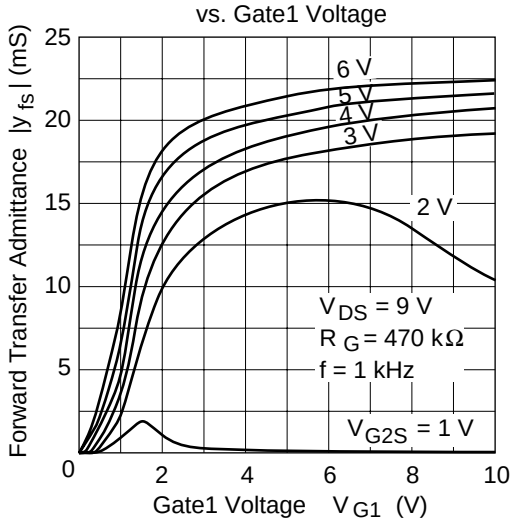
Drain Current vs. Gate1 Voltege



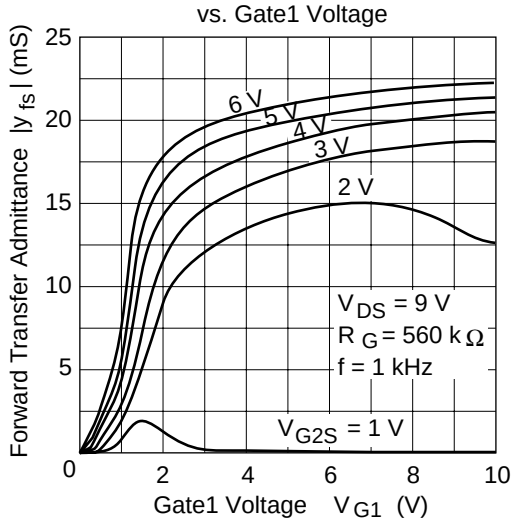
Drain Current vs. Gate1 Voltege



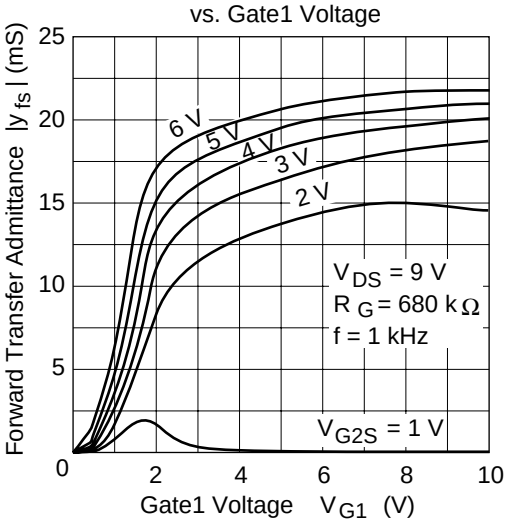
Forward Transfer Admittance vs. Gate1 Voltage



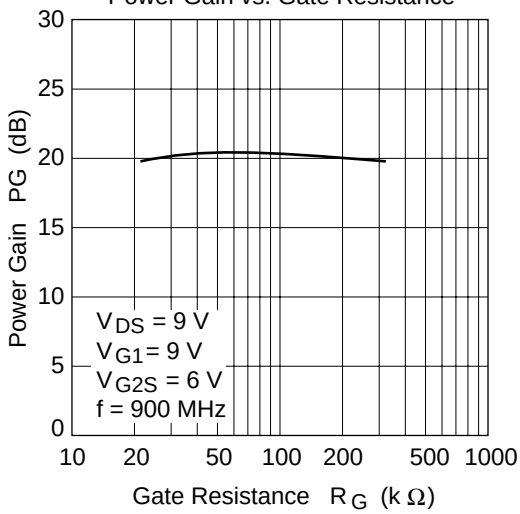
Forward Transfer Admittance vs. Gate1 Voltage



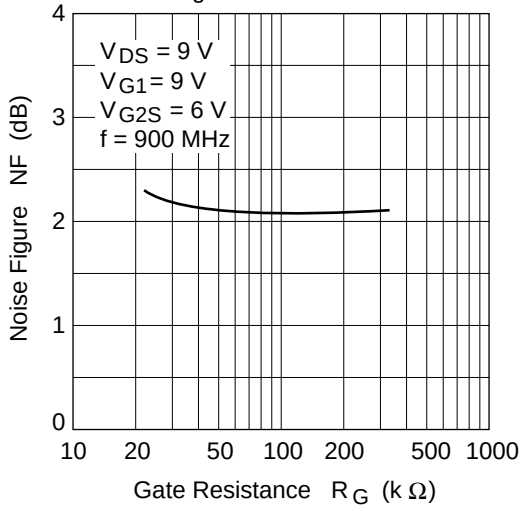
Forward Transfer Admittance vs. Gate1 Voltage



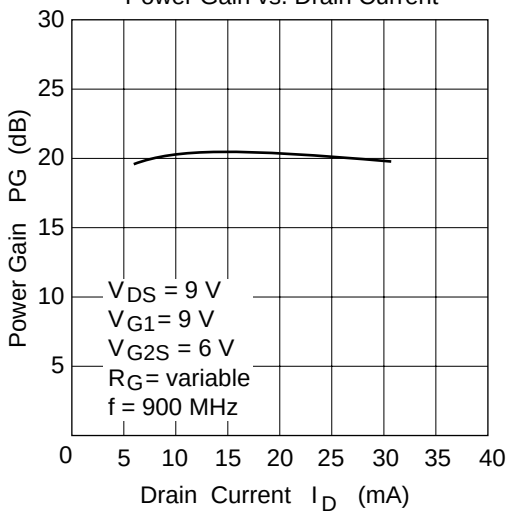
Power Gain vs. Gate Resistance



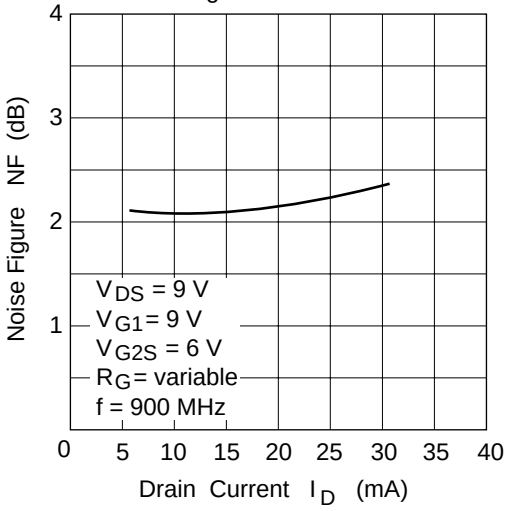
Noise Figure vs. Gate Resistance



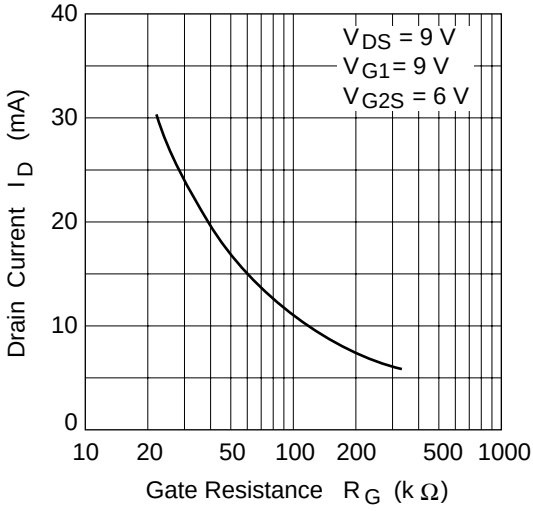
Power Gain vs. Drain Current



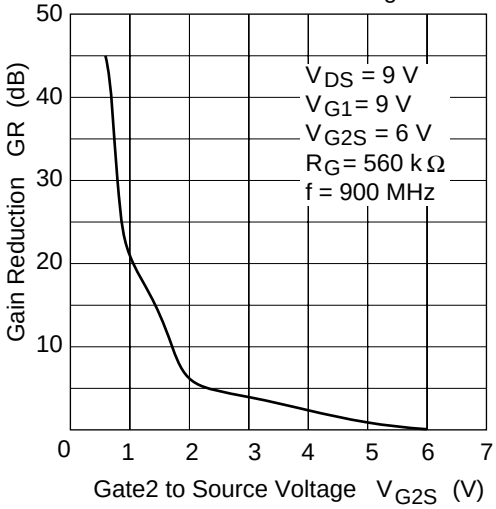
Noise Figure vs. Drain Current



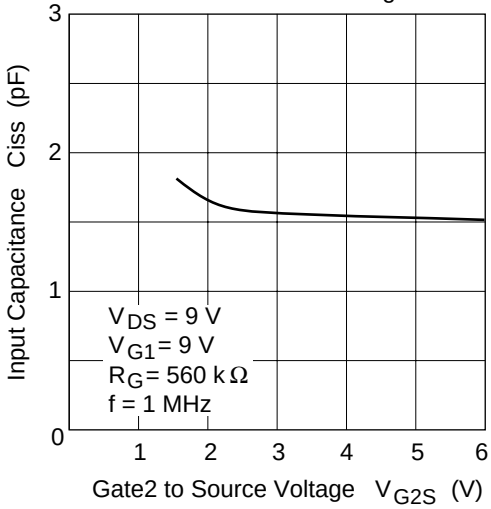
Drain Current vs. Gate Resistance



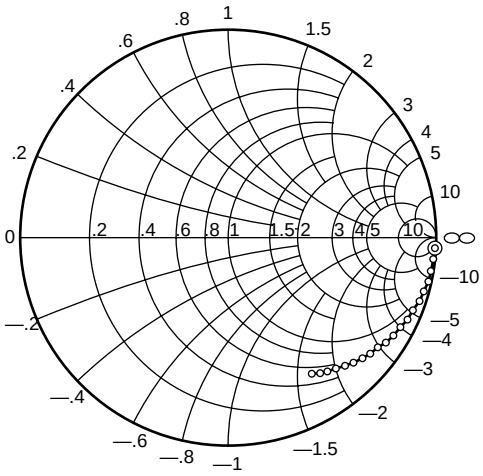
Gain Reduction vs.
Gate2 to Source Voltage



Input Capacitance vs.
Gate2 to Source Voltage

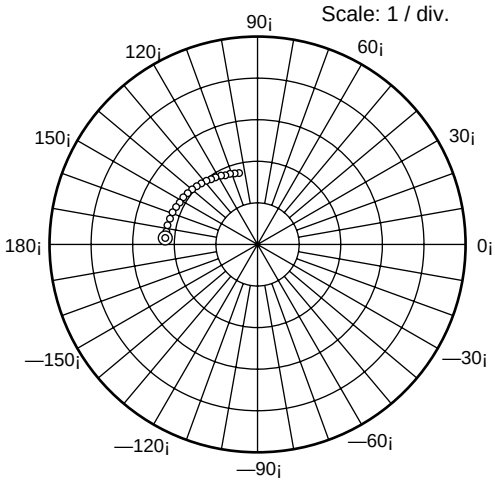


S11 Parameter vs. Frequency



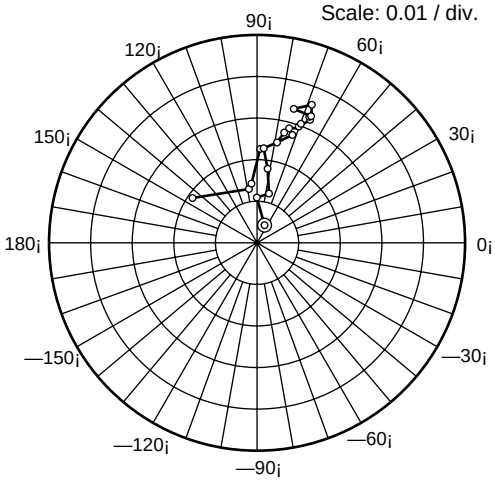
Test Condition : V_{DS}= 9 V , V_{G1}= 9 V
V_{G2S} = 6 V , R_G = 560 kΩ
50 1000 MHz (50 MHz step)

S21 Parameter vs. Frequency



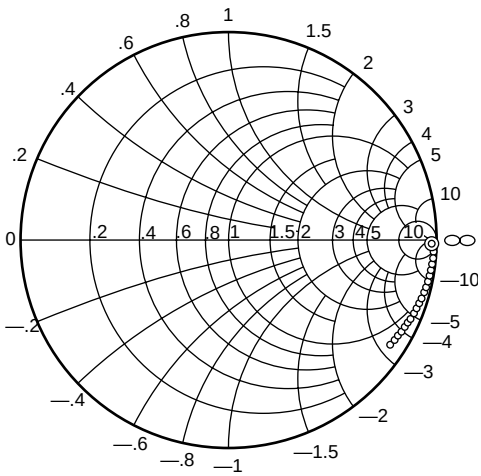
Test Condition : V_{DS}= 9 V , V_{G1}= 9 V
V_{G2S} = 6 V , R_G = 560 kΩ
50 1000 MHz (50 MHz step)

S12 Parameter vs. Frequency



Test Condition : V_{DS}= 9 V , V_{G1}= 9 V
V_{G2S} = 6 V , R_G = 560 kΩ
50 1000 MHz (50 MHz step)

S22 Parameter vs. Frequency



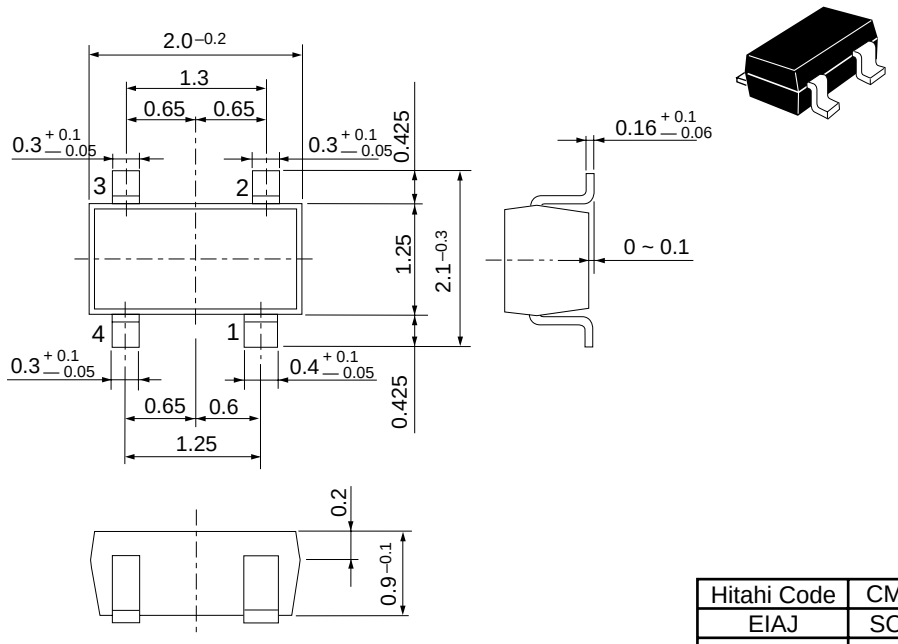
Test Condition : V_{DS}= 9 V , V_{G1}= 9 V
V_{G2S} = 6 V , R_G = 560 kΩ
50 1000 MHz (50 MHz step)

Sparameter (V_{DS} = V_{G1} = 9V, V_{G2S} = 6V, R_G = 560kΩ, Zo = 50Ω)

	S11		S21		S12		S22	
f (MHz)	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
50	0.995	–2.9	2.22	176.0	0.00046	66.9	0.977	–1.0
100	0.991	–6.0	2.21	172.0	0.00109	90.4	0.987	–3.2
150	0.987	–9.4	2.21	168.0	0.00122	76.5	0.987	–5.0
200	0.985	–12.4	2.19	163.6	0.00180	81.9	0.985	–6.7
250	0.975	–15.4	2.18	159.3	0.00228	86.0	0.983	–8.4
300	0.969	–18.4	2.15	155.3	0.00246	78.8	0.981	–10.0
350	0.954	–21.5	2.12	151.7	0.00273	76.2	0.979	–11.7
400	0.948	–24.6	2.11	147.6	0.00331	66.9	0.976	–13.4
450	0.933	–27.5	2.08	143.7	0.00334	74.7	0.973	–14.9
500	0.923	–30.7	2.05	139.9	0.00357	68.4	0.969	–16.8
550	0.912	–33.6	2.02	136.2	0.00328	67.5	0.965	–18.3
600	0.892	–36.3	1.99	123.9	0.00305	69.8	0.961	–19.9
650	0.882	–39.3	1.96	128.7	0.00322	66.7	0.958	–21.5
700	0.868	–42.0	1.92	125.4	0.00297	70.3	0.953	–23.4
750	0851	–45.0	1.90	122.0	0.00286	74.4	0.948	–24.7
800	0.834	–47.7	1.87	117.9	0.00273	71.9	0.944	–26.2
850	0.815	–50.6	1.83	114.9	0.00226	88.1	0.940	–27.9
900	0.801	–53.5	1.82	111.2	0.00143	95.5	0.934	–29.4
950	0.788	–55.9	1.79	107.8	0.00131	98.6	0.931	–31.0
1000	0.768	–58.5	1.77	104.4	0.00189	145.2	0.925	–32.9

Package Dimensions

Unit: mm



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EIAJ	SC-82AB
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